

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030238	Application No. 10/707,842		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant Haining S.YANG, et al..					
		Filing Date 01/16/2004		Group 2812			
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EXAMINER /Walter Lindsay Jr/ (06/06/2006)				DATE CONSIDERED 06/06/2006			
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